

# 國立中山大學 107 學年度碩士暨碩士專班招生考試試題

科目名稱：電子學【電機系碩士班甲組】

題號：431009

※本科目依簡章規定「可以」使用計算機（廠牌、功能不拘）（問答申論題） 共 1 頁第 1 頁

1. (20%) Figure 1 shows a MOSFET circuit with the  $V_{DC} = 5\text{ V}$ ,  $R_{sig} = 120\text{ k}\Omega$ ,  $R_{G1} = 300\text{ k}\Omega$ ,  $R_{G2} = 200\text{ k}\Omega$ ,  $R_D = 2\text{ k}\Omega$ ,  $R_S = 1\text{ k}\Omega$ ,  $R_L = 1\text{ k}\Omega$ . The threshold voltage  $V_{TH}$  and  $\mu C_{ox}W/L$  of MOSFET are  $-1\text{ V}$  and  $2\text{ mA/V}^2$  respectively. Neglect the channel length modulation effect. (a) Please find the DC drain current  $I_D$ . (b) For AC analysis, please find the input resistance  $R_{in}$ , output resistance  $R_{out}$  and overall gain  $v_o/v_{sig}$ . (5%\*4)
2. (20%) Figure 2 shows a BJT circuit with the  $V_{DC} = 5\text{ V}$ ,  $R_{sig} = 120\text{ k}\Omega$ ,  $R_{B1} = 300\text{ k}\Omega$ ,  $R_{B2} = 200\text{ k}\Omega$ ,  $R_E = 5\text{ k}\Omega$ ,  $R_C = 2\text{ k}\Omega$ ,  $R_L = 5\text{ k}\Omega$ . The BJT has  $|V_{BE}| \approx 0.7\text{ V}$ ,  $\beta = 100$ , thermal voltage  $V_T = 25\text{ mV}$ . Neglect the Early effect. (a) Please find the DC collector current  $I_C$ . (b) For AC analysis, please find the input resistance  $R_{in}$ , output resistance  $R_{out}$  and overall gain  $v_o/v_{sig}$ . (5%\*4)
3. (30%) The amplifier shown in Fig. 3 has  $V_{DC} = 1.5\text{ V}$ ,  $R_{sig} = R_L = 1\text{ k}\Omega$ ,  $R_C = 1\text{ k}\Omega$ ,  $R_B = 47\text{ k}\Omega$ . The BJT has  $|V_{BE}| \approx 0.7\text{ V}$ ,  $\beta = 100$ ,  $C_\mu = 0.8\text{ pF}$ ,  $f_T = 600\text{ MHz}$ , and thermal voltage  $V_T = 25\text{ mV}$ . Assume the coupling capacitors to be very large. Neglect the Early effect. (a) Find the collector current of the transistor. (b) Find the overall gain  $v_o/v_{sig}$  and the input resistance  $R_{in}$  at midband frequency. (c) Find the high frequency response  $f_H$ . (5%,5%,10%,10%)
4. (30%) Consider the BiCMOS amplifier shown in Fig. 4 has  $V_{DC} = 5\text{ V}$ ,  $R_{sig} = 100\text{ k}\Omega$ ,  $R_G = 10\text{ M}\Omega$ ,  $R_S = 6.8\text{ k}\Omega$ ,  $R_C = 3\text{ k}\Omega$ ,  $R_L = 1\text{ k}\Omega$ ,  $C_1 = 0.1\text{ }\mu\text{F}$ ,  $C_2 = 1\text{ }\mu\text{F}$ . The BJT has  $|V_{BE}| \approx 0.7\text{ V}$ ,  $\beta = 200$ ,  $C_\mu = 0.8\text{ pF}$ ,  $f_T = 600\text{ MHz}$ , and thermal voltage  $V_T = 25\text{ mV}$ . The MOSFET has  $V_{TH} = 1\text{ V}$ ,  $\mu C_{ox}W/L = 2\text{ mA/V}^2$ , and  $C_{gs} = C_{gd} = 1\text{ pF}$ . Neglect the Early effect and channel length modulation effect. (a) Consider the DC bias circuit. Neglect the base current of Q2 in determining the current in Q1. Find the DC drain current in Q1 and collector current in Q2. (b) Consider the circuit at low frequencies. Determine the frequency of the poles due to  $C_1$  and  $C_2$ . (c) Consider the circuit at higher frequencies. Use open-circuit time constants to estimate  $f_H$ . (5%,5%,5%,5%,10%)

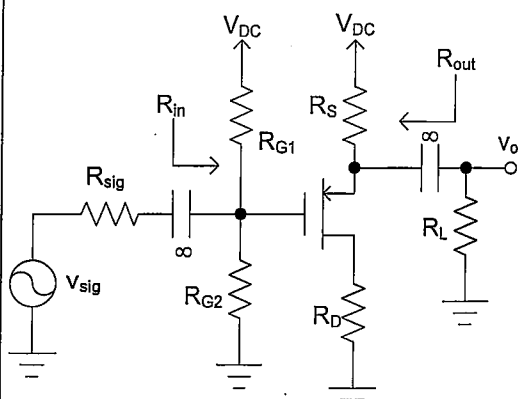


Figure 1

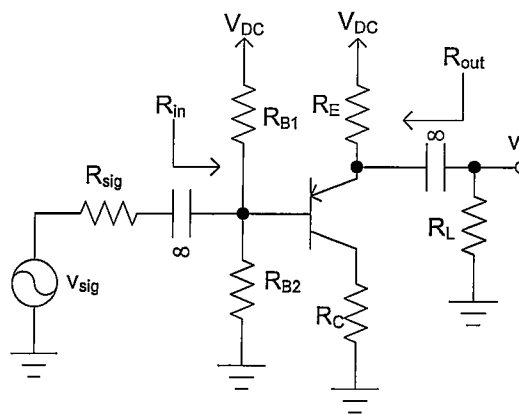


Figure 2

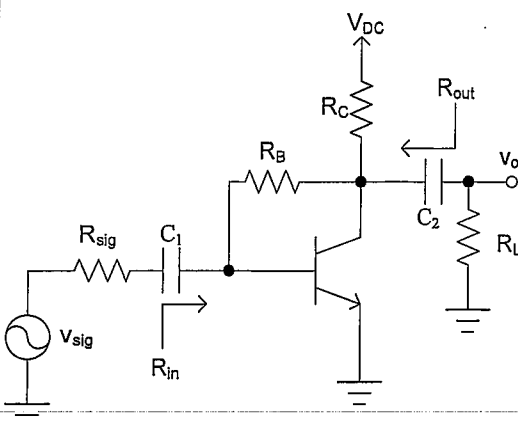


Figure 3

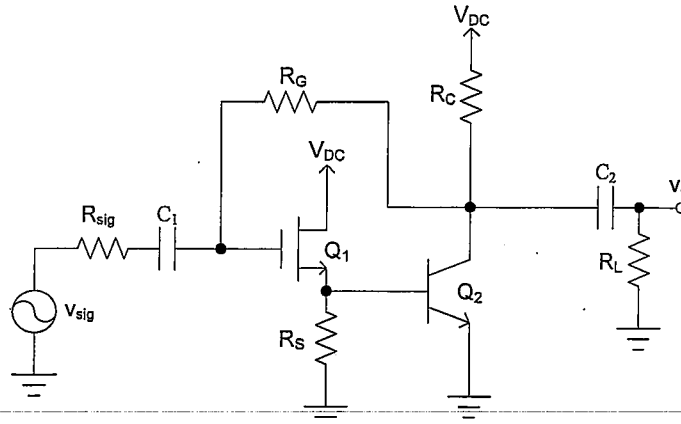


Figure 4